

### ABSTRACT OF THE DISCLOSURE

A method of low-damage, anisotropic etching of substrates including mounting the substrate upon a mechanical support located within an ac or dc plasma reactor. The mechanical support is independent of the plasma reactor generating apparatus and capable of being electrically biased. The substrate is subjected to a plasma of low-energy electrons and a species reactive with the substrate. An additional structure capable of being electrically biased can be placed within the plasma to control further the extraction or retardation of particles from the plasma.

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